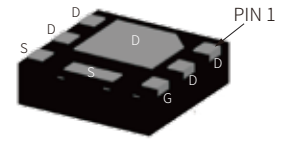
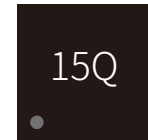


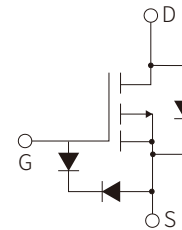
FEATURES

- | Side wettable flanks for optical solder inspection
- | ElectroStatic Discharge (ESD) protection > 1 kV HBM (class H1C)
- | Trench MOSFET technology
- | Meet AEC-Q101 Requirements


DFN2020-6L

Marking

APPLICATION

- | DC to DC conversion
- | High-speed line driver
- | Low-side load switch
- | Switching circuits


Schematic Symbol

APPROVALS

RoHS	Compliance with 2011/65/EU
HF	Compliance with IEC61249-2-21:2003

ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-20	V
Drain Current (Pulsed)	I_{DM}	-28	A
Drain Current	I_D	-7	A
Gate-Source Voltage $T_c=25^\circ\text{C}$	V_{GS}	± 12	V
Total Power Dissipation	P_{tot}	19	W
Junction Temperature	T_J	-55 to 175	$^\circ\text{C}$
Storage Temperature	T_{STG}	-55 to 175	$^\circ\text{C}$
Thermal Resistance –Junction to Ambient	$R_{\theta JA}$	76	$^\circ\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS (T_A=25°C)

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =-250μA	-20			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =-250μA	-0.45	-0.65	-1.0	V
Drain Leakage Current	I _{DSS}	V _{DS} =-20V, V _{GS} =0V			-1	μA
Gate Leakage Current	I _{GSS}	V _{GS} =±10V, V _{DS} =0V			±10	μA
On-State Resistance	R _{DS(on)}	V _{GS} =-4.5V, I _D =-2.0A		27	35	mΩ
		V _{GS} =-2.5V, I _D =-1.5A		34	42.5	mΩ
Diode Characteristics						
Diode Forward Voltage	V _{SD}	I _S =-2A, V _{GS} =0V		-0.8	-1.2	V
Reverse Recovery Time	t _{rr}	I _S =-2A, V _{GS} =0V di _{SD} /dt=-100A/μs V _{DS} =-10V, T _j =25 °C		17		nS
Reverse Recovery Charge	Q _{rr}			5		nC
Dynamic Characteristics^b						
Input capacitance	C _{iss}	V _{GS} =0V, V _{DS} =-10V, Frequency = 1 MHz		1025		pF
Output capacitance	C _{oss}			137		pF
Reverse transfer capacitance	C _{rss}			113		pF
Turn-on Delay Time	t _{d(on)}	V _{DS} =-10V, V _{GS} =-4.5V R _G =6Ω, I _D =-5.8A		6		nS
Turn-on Rise Time	t _r			17		nS
Turn-Off Delay Time	t _{d(off)}			23		nS
Turn-Off Fall Time	t _f			19		nS
Gate Charge Characteristics^b						
Total Gate Charge	Q _g	V _{DS} =-10V, V _{GS} =-4.5V, I _D =-5.8A		10.6	16	nC
Gate-Source Charge	Q _{gs}			2.1		nC
Gate-Drain Charge	Q _{gd}			3.6		nC

PARAMETER CHARACTERISTIC CURVE

Figure 1: Output characteristics: drain current as a function of drain-source voltage; typical values

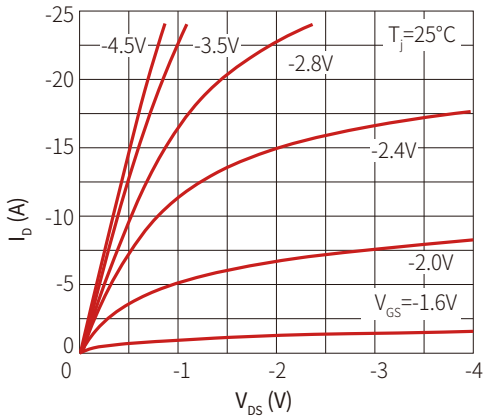


Figure 2: Sub-threshold drain current as a function of gate-source voltage

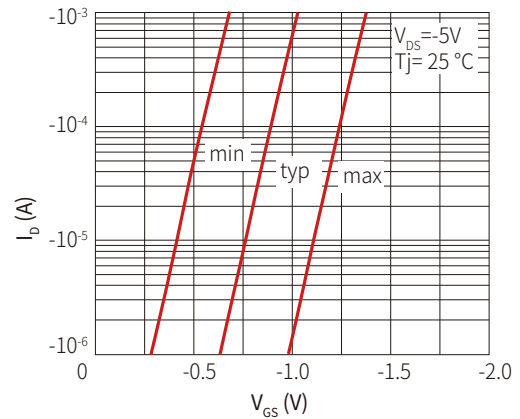


Figure 3: Drain-source on-state resistance as a function of drain current; typical values

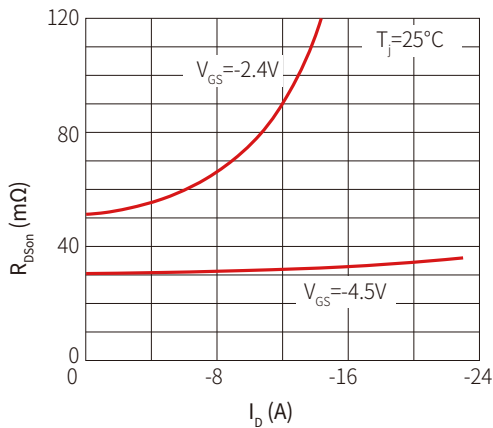


Figure 4: Drain-source on-state resistance as a function of gate-source voltage; typical values

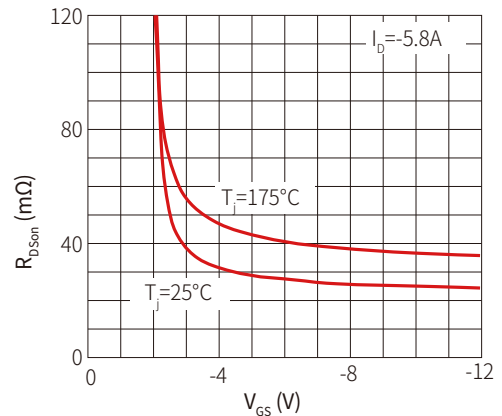


Figure 5: Transfer characteristics: drain current as a function of gate-source voltage; typical values

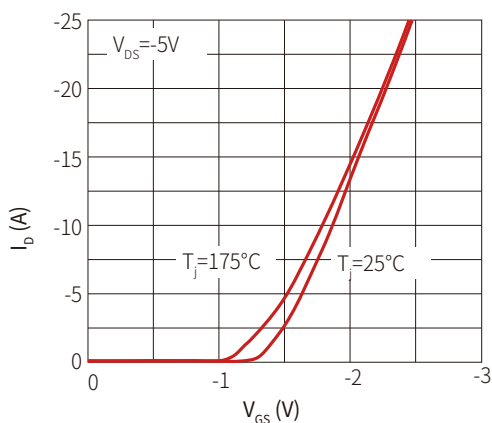


Figure 6: Gate-source threshold voltage as a function of junction temperature

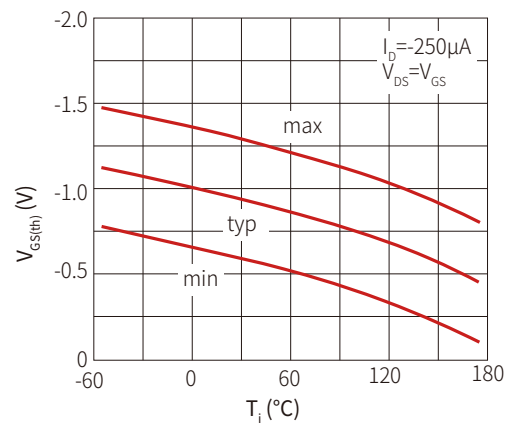


Figure 7: Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

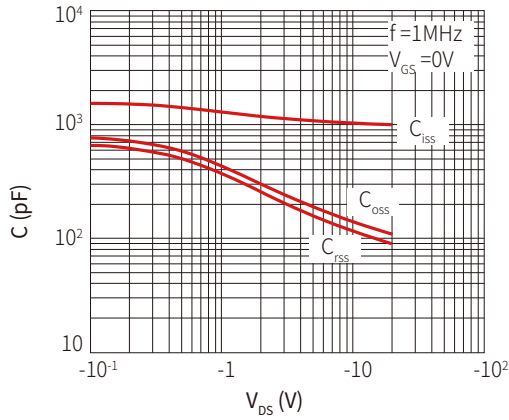


Figure 8: Source current as a function of source-drain voltage; typical values

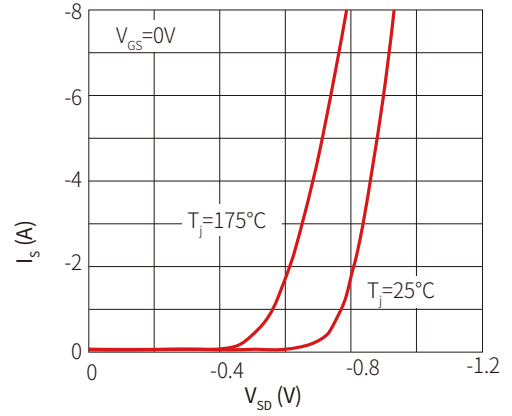


Figure 9: Gate-source voltage as a function of gate charge; typical values

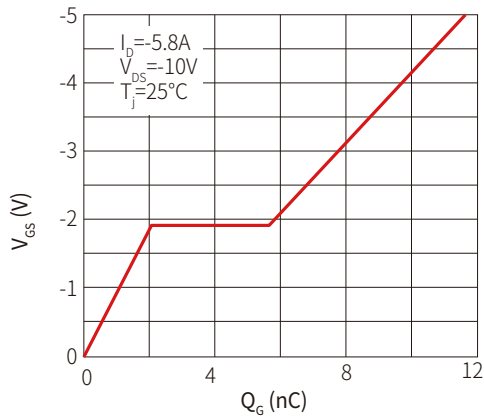


Figure 10: Normalized continuous drain current as a function of solder point temperature

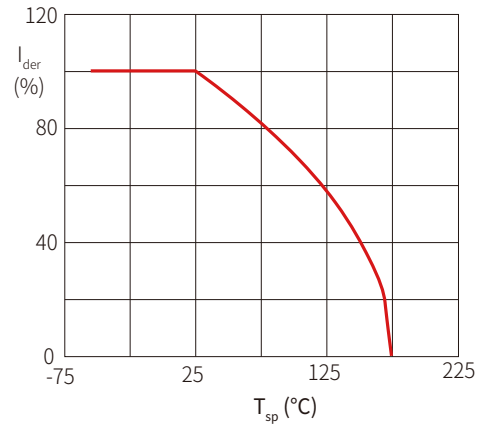


Figure 11: Normalized total power dissipation as a function of solder point temperature

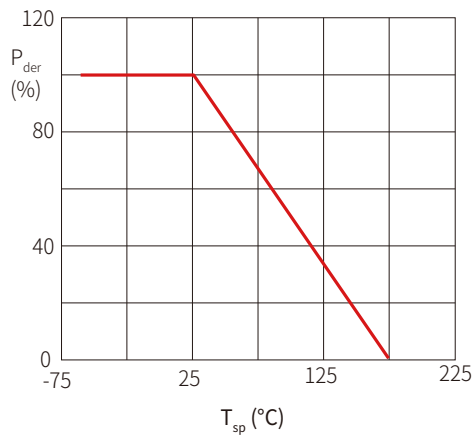


Figure 12: Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain source voltage

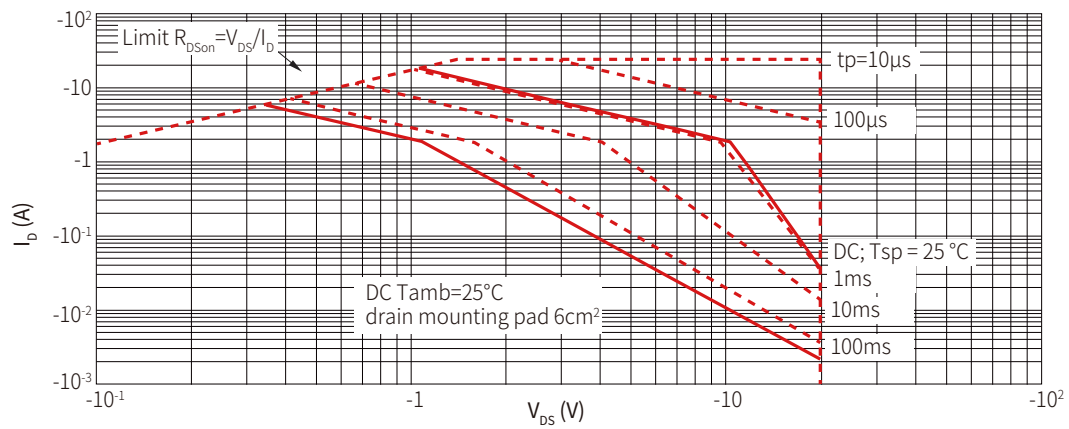
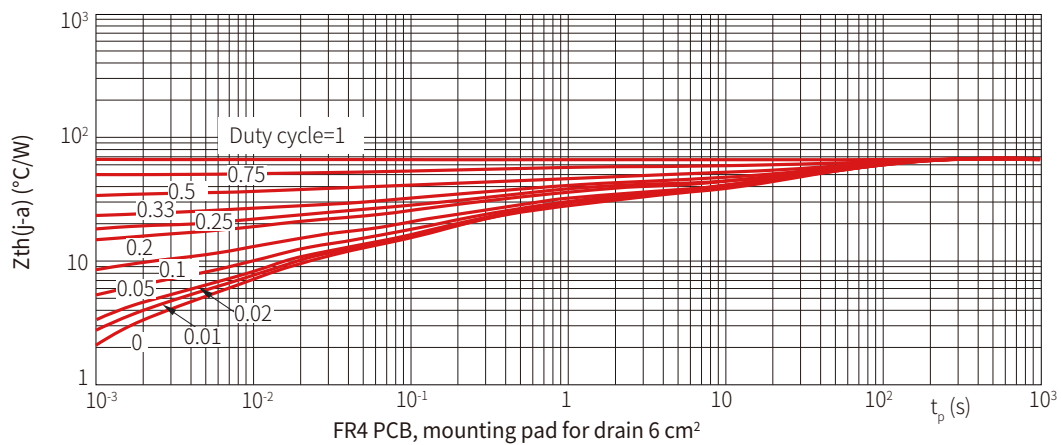
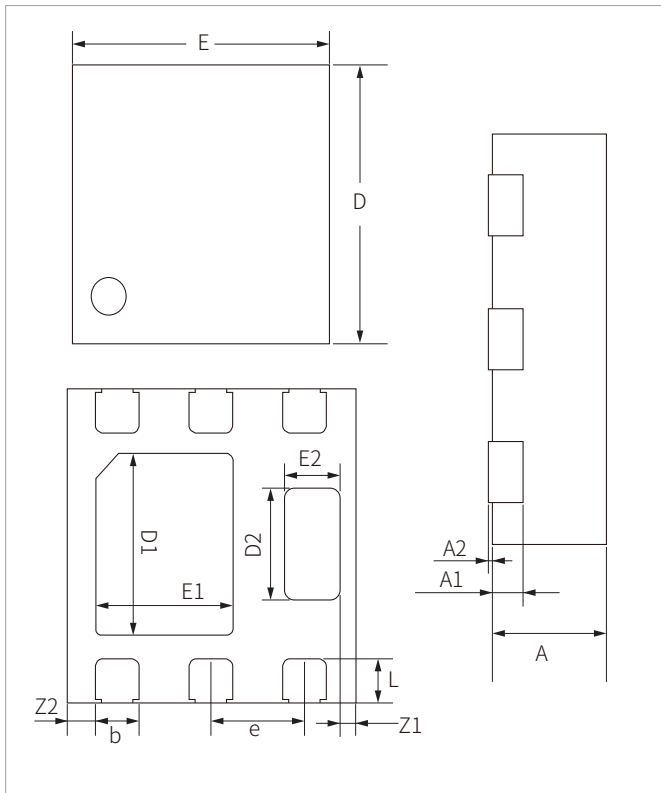


Figure 13: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values



DFN2020-6L PACKAGE INFORMATION



Ref.	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
D	1.95	2.00	2.05	0.077	0.079	0.081
E	1.95	2.00	2.05	0.077	0.079	0.081
D1	1.10	1.15	1.20	0.043	0.045	0.047
E1	0.90	0.95	1.00	0.035	0.037	0.039
D2	0.65	0.70	0.75	0.026	0.028	0.030
E2	0.33	0.38	0.43	0.013	0.015	0.017
L	0.23	0.275	0.33	0.009	0.011	0.013
b	0.25	0.30	0.35	0.010	0.012	0.014
e	0.65BSC			0.026BSC		
A	0.40	0.50	0.60	0.016	0.020	0.024
A1	0.150REF			0.006REF		
A2	0.00	-	0.05	0.00	-	0.002
Z1	0.06	0.11	0.16	0.002	0.004	0.006
Z2	0.15	0.20	0.25	0.006	0.008	0.010

ORDERING INFORMATION

Part Number	Component Package	QTY/Reel	Reel Size
SPM3415RQ	DFN2020-6L	3000PCS	7"

Headquarters

No.3387 Shendu Road
Pujiang I&E Park
Minhang Shanghai China
201000

Hotline

400-021-5756

Web

<https://www.semiware.com>

Sales Center

Tel: 86-21-3463-7458
Email: sales18@semiware.com

Customer Service

Tel: 86-21-5484-1001
Email: sales17@semiware.com

Technical Support

Tel: 86-21-3463-7654
Email: fae01@semiware.com

Complaint & Suggestions

Tel: 86-21-3463-7172
Ext: 8868
Email: cs03@semiware.com

By QR Code

Website



Wechat

To find your local partner within Semiware' s global website: www.semiware.com

© 2022 Semiware Semiconductor Inc.

The content of this document has been carefully checked and understood. However, neither Semiware nor its subsidiaries assume any liability whatsoever for any errors or inaccuracies of this document and the consequences thereof. Published specifications are subject to change without notice. Product suitability for any area of application must ultimately be determined by the customer. In all cases, products must never be operated outside their published specifications. Semiware does not guarantee the availability of all published products. This disclaimer shall be governed by substantive Chinese law and resulting disputes shall be settled by the courts at the place of business of Semiware. Latest publications and a complete disclaimer can be downloaded from the Semiware website. All trademarks recognized.